

Application No.: 10/669940  
Docket No.: CL2173USNA

Page 2

**Listing of Claims**

Claims 1-13 (Cancelled).

14. (Currently Amended) A transistor comprising a semiconductor component comprising an undoped transparent metal oxide disposed between and in contact with a source electrode and a drain electrode.
15. (Cancelled).
16. (Currently Amended) A flat panel display comprising one or an array of transparent oxide semiconductor transistors ~~as described by~~ as recited in Claim 14.
17. (Currently Amended) An active matrix imager comprising an array of transparent oxide semiconductor transistors ~~as described by~~ as recited in Claim 14.
18. (Currently Amended) A sensor comprising an array of transparent oxide semiconductor transistors ~~as described by~~ as recited in Claim 14.
19. (Currently Amended) A rf price label comprising an array of transparent oxide semiconductor transistors ~~as described by~~ as recited in Claim 14.
20. (Currently Amended) A rf identification tag comprising an array of transparent oxide semiconductor transistors ~~as described by~~ as recited in Claim 14.
21. (Currently Amended) A rf inventory tag comprising an array of transparent oxide semiconductor transistors ~~as described by~~ as recited in Claim 14.
22. (Currently amended) The transistor of Claim 14 deposited on a flexible substrate .
23. (Currently amended) The transistor of Claim 14 further comprising a gate electrode, and wherein said source, drain and gate electrodes are fabricated from a material selected from the group consisting of zinc oxide, indium oxide, tin oxide, and cadmium oxide.
24. (Original) The transistor of Claim 22 further comprising a gate dielectric fabricated from a material selected from the group consisting of zinc oxide, indium oxide, tin oxide, and cadmium oxide.